TOSHIBA 1200JXH23

TENTATIVE

TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

1200JXH23

HIGH SPEED RECTIFIER APPLICATIONS

Repetitive Peak Reverse Voltage: $V_{RRM} = 6000V$

Average Forward Current $: I_{F(AV)} = 1200A$

Double Side Cooling

MAXIMUM RATING

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	v_{RRM}	6000	V
Non-Repetitive Peak Reverse Voltage (Non-Repetitive ≤ 5 ms, $T_j \leq 0 \sim 125$ °C)	V _{RSM}	6300	V
Average Forward Current	I _{F (AV)}	1200	A
Peak One Cycle Surge Forward Current (Non-Repetitive, 10ms Width Half Sine Waveform)	$I_{ ext{FSM}}$	15000	A
Junction Temperature Range	Tj	-40~125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~125	$^{\circ}\mathrm{C}$
Mounting Force	_	37.3±7.8	kN

Unit in mm $2 - \phi 3.5 \pm 0.2$ depth 2.1 ± 0.4 φ120MAX ① CATHODE ② ANODE **JEDEC EIAJ**

3-120C1A

Weight: 1300g

TOSHIBA

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	TYP.	MAX.	UNIT
Repetitive Peak Reverse Current	I_{RRM}	V _{RRM} =4500V, T _j =125°C	_	150	mA
Peak Forward Voltage	$V_{\mathbf{FM}}$	I_{FM} =3800A, T_j =125°C		4.4	V
Reverse Recovery Charge	Q_{rr}	$I_{ m F} = 1200 m A, \ T_{ m j} = 125 m ^{\circ} C \ di_{ m F} / dt = 100 m A / \ \mu s$	_	4000	μC
Thermal Resistance	R _{th (j-f)}	Junction to Fin	_	0.012	°C/W

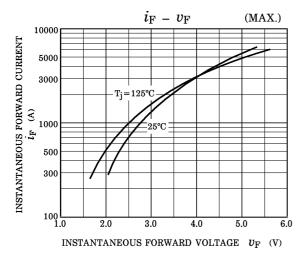
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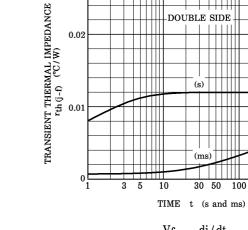
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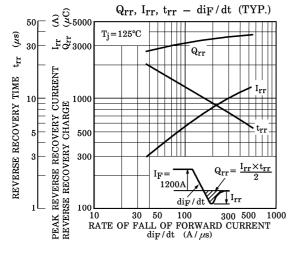
(MAX.)

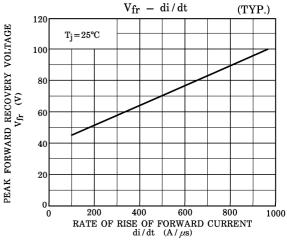
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0.02





 $r_{th}(j-f) - t$

DOUBLE SIDE

(s)